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## (54) Title of the invention : A METHOD FOR PREPARATION OF COBALT-GRAPHENE FERROMAGNETIC CONTACTS BASED SPIN-FIELD EFFECT TRANSISTORS

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## (57) Abstract:

The present invention relates to a method for preparation of cobalt-graphene ferromagnetic contacts based spin-field effect transistors. The object is to provide Datta and Das type s-FET and Back-Gate type s-FET with cobalt-graphenenano sheets based ferromagnetic electrodes. In the construction of s-FET, the Co-Graphenenano sheets based ferromagnetic electrode having Ohmic contact behavior is used. Notable value magneto resistanceis obtained for both devices as a function of temperature and gate voltage. Magneto resistance monotonically reduces as temperature increases. For greater insight into about the functioning of device, spin-polarization values are estimated at different temperatures. Switching action in both the devices are analyzed and finally it is found that Datta and Das type s-FET shows appropriate switching action. Following invention is described in detail with the help of Figure 1 of sheet 1 showing Datta and Das Type s-FET structure and Figure 2 of sheet 2 showing back-gate type s-FET structure.

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